DOCUMENT CHANGE REQUEST					
DCR number	1699	Changes re	quired for: Gen	eral	Originator: Steve Jeffery
Date: 2025/01	/28         Date sent: 2024/10/22				Organisation: ESCC Executive
Status: IMPLEMENTED					
Title:	INTEGRATED CIRCUITS, SILICON MONOLITHIC, CMOS DIGITAL, MEMORY, RADIATION				
Number:	9304/010 Issue: 3			3	
Other documents affected:					
Page:					
33					
Paragraph:					
New Para. 2.1.1.2, Deviations from Qualification and Periodic Tests - Chart F4A					
Original wording:					
-					
Proposed wording:					
See the attached MSWord file ESCC9304010iss4 Draft A for DCR review.					
Justification:					
Technically acceptable; STMicroelectronics have advised that the bond strength sampling changes have already been discussed with ESA and CNES.					
N.B.: this DCR has been raised by the ESCC T.W. following a request to do so from STMicroelectronics Pauline Le Paih.					
Attachments:					
escc9304010iss4_draft_a_for_dcr_review.docx					
Modifications:					
<ul> <li>Para. 2.1.1.2(a): Quantity of leads tested is corrected to "15".</li> <li>Para. 2.1.1.2(b): Para. is re-worded for clarification and to delete erroneous "applicable to Variant ##".</li> <li>New Deviation against Moisture Resistance (applicable to Variant 01 only) is added.</li> </ul>					
Approval signature:					
Date signed:					

2025-01-28